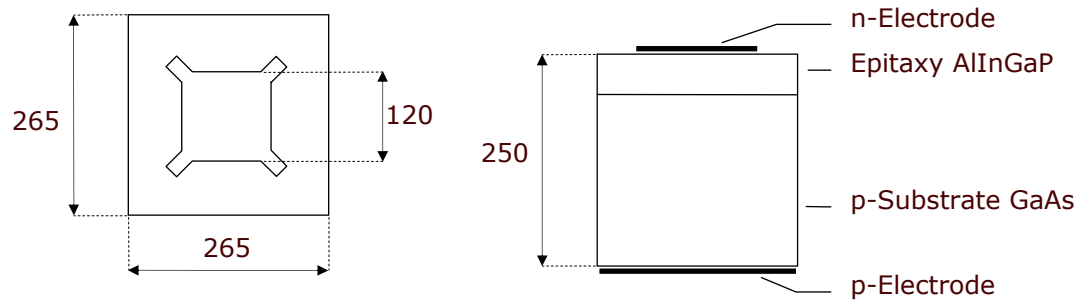


<b>RED</b>	<b>Item No.: 194170</b>
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1. This specification applies to AlInGaP / GaAs LED Chips
2. Structure
  - 2.1 Mesa structure
  - 2.2 Electrodes
 

p-side (anode)	Au alloy or Al
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Chip thickness could also be 180  $\mu\text{m}$  or 210  $\mu\text{m}$

Wire-bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

<i>Parameter</i>	<i>Symbol</i>	<i>Conditions</i>	<i>min</i>	<i>typ</i>	<i>max</i>	<i>Unit</i>
Forward voltage	$V_F$	$I_F = 20 \text{ mA}$		1,90	2,30	V
Reverse current	$I_R$	$V_R = 5 \text{ V}$			10	$\mu\text{A}$
Luminous intensity *	$I_V$	$I_F = 20 \text{ mA}$		20		mcd
Peak wavelength	$\lambda_p$	$I_F = 20 \text{ mA}$		655		nm

Brightness measurement at OSA on gold plate

5. Packing
  - Dice on adhesive film with 1) wire-bond side on top
  - 2) back contact on top
6. Labeling

Type	Lot No.	I <sub>v</sub> typ	Quantity
		min	
		max	